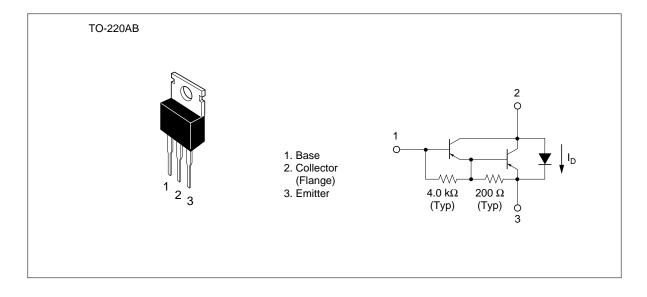
Silicon PNP Triple Diffused

HITACHI

Application

Low frequency power amplifier

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

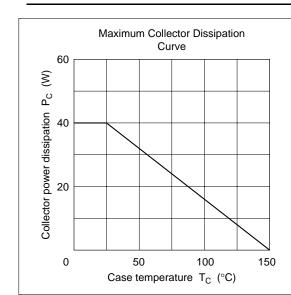
| Item | Symbol | Ratings | Unit | |
|------------------------------|-------------------|-------------|------|--|
| Collector to emitter voltage | V_{CBO} | -60 | V | |
| Collector to emitter voltage | V_{CEO} | -60 | V | |
| Emitter to base voltage | V_{EBO} | – 7 | V | |
| Collector current | I _c | -8 | А | |
| Collector peak current | C(peak) | -12 | Α | |
| Collector power dissipation | P _c *1 | 40 | W | |
| Junction temperature | Tj | 150 | °C | |
| Storage temperature | Tstg | -55 to +150 | °C | |
| C to E diode forward current | I _D *1 | 8 | Α | |

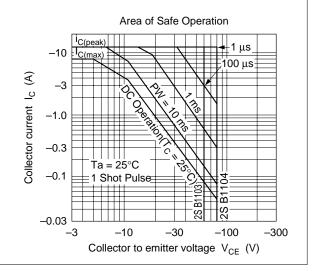
Note: 1. Value at $T_c = 25$ °C.

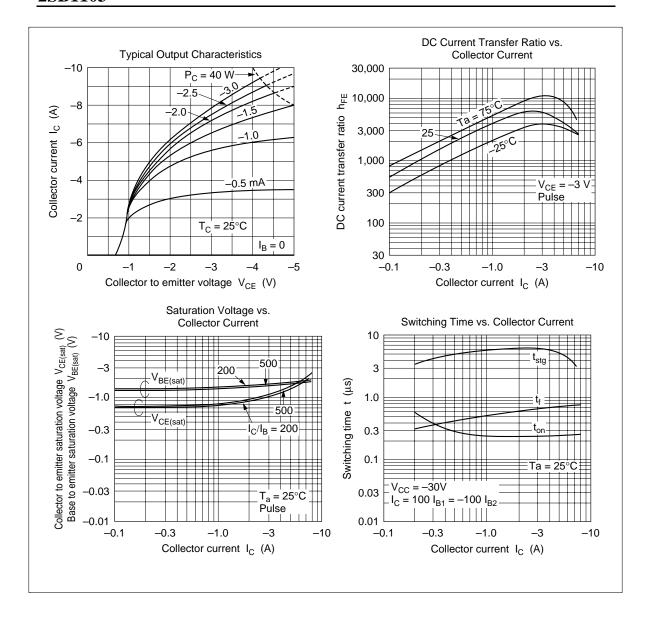
Electrical Characteristics ($Ta = 25^{\circ}C$)

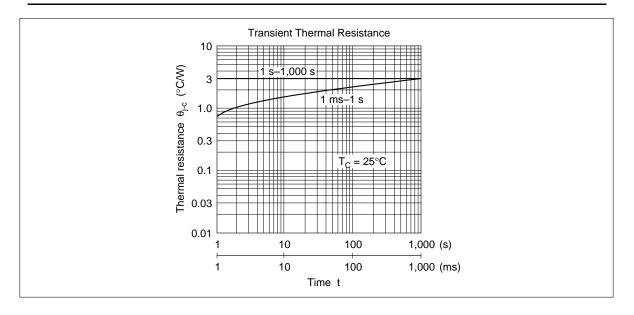
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|-----------------------|-----------|-----|-------|------|---|
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | -60 | _ | _ | V | $I_{\text{C}} = -25 \text{ mA}, R_{\text{BE}} =$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | -7 | _ | _ | V | $I_{\rm E} = -50$ mA, $I_{\rm C} = 0$ |
| Collector cutoff current | I _{CBO} | _ | _ | -100 | μΑ | $V_{CB} = -60 \text{ V}, I_{E} = 0$ |
| | I _{CEO} | _ | _ | -10 | μΑ | $V_{CE} = -50 \text{ V}, R_{BE} =$ |
| DC current tarnsfer ratio | h _{FE} | 1000 | _ | 20000 | | $V_{CE} = -3 \text{ V}, I_{C} = -4 \text{ A}^{*1}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)1}$ | _ | _ | -1.5 | V | $I_{\rm C} = -4 \text{ A}, I_{\rm B} = -8 \text{ mA}^{*1}$ |
| | V _{CE(sat)2} | _ | _ | -3.0 | _ | $I_{\rm C} = -8 \text{ A}, I_{\rm B} = -80 \text{ mA}^{*1}$ |
| Base to emitter saturation voltage | $V_{BE(sat)1}$ | _ | _ | -2.0 | V | $I_{\rm C} = -4 \text{ A}, I_{\rm B} = -8 \text{ mA}^{*1}$ |
| | V _{BE(sat)2} | _ | _ | -3.5 | | $I_{\rm C} = -8 \text{ A}, I_{\rm B} = -80 \text{ mA}^{*1}$ |
| C to E diode forward voltage | V _D | _ | _ | 3.0 | V | I _D = 8 A* ¹ |
| Turn on time | t _{on} | _ | 0.5 | | μs | I _C = -4 A, |
| Storage time | t _{stg} | _ | 3.0 | | | $I_{B1} = -I_{B2} = -8 \text{ mA}$ |
| Fall time | t _f | _ | 1.0 | | _ | |

Note: 1. Pulse Test.









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